Notice of Allowability	Application No.	Applicant(s)
	10/710,488	CHUNG ET AL.
	Examiner	Art Unit
	Shamim Ahmed	1765
The MAILING DATE of this communication appeals of the communication appeals of the communication appeals of the communication appeals of the Office of MAILING DATE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIPS of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this apport or other appropriate communication GHTS. This application is subject to	olication. If not included will be mailed in due course. THIS
1. This communication is responsive to 3/7/06.		
2. The allowed claim(s) is/are <u>1-22</u> .		
3. Acknowledgment is made of a claim for foreign priority una   All   b) Some*   c) None   No	been received in Application Nocuments have been received in this rece	complying with the requirements  S AMENDMENT or NOTICE OF tion is deficient.  948) attached  ffice action of the back) of the complying with the back of the submitted. Note the
Attachment(s)  1. ☑ Notice of References Cited (PTO-892)  2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)  3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date  4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	6. Interview Summary Paper No./Mail Date 8), 7. Examiner's Amendm	è

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## **REASONS FOR ALLOWANCE**

- 1. The following is an examiner's statement of reasons for allowance: The prior art fail to teach an etching process including the step of forming a plurality of microtrenches at the edges of a residual hard mask layer in the exposed region, wherein the residual hard mask layer remains in the exposed region as claimed.
- 2. The closest prior art Tsai et al (6,878,646) teach a process for reducing the critical dimension of a hard mask but fail to teach a process of reducing pattern pitch on a substrate including the steps of etching the hard mask layer using a patterned photoresist layer, while a residual hard mask layer remains in the exposed region and a plurality of micro-trenches are formed at the edges of the residual hard mask layer in the exposed region as claimed.
- 3. Another closest prior art Zheng (USP 6,475,922) teaches the use of a hard mask (230) on a material layer of polysilicon (220) to be etched using a pattern photoresist masking layer (240)(see figures 2A-2C) but fails to teach leaving a portion of hard mask layer in the exposed region (250) in which micro-trenches are formed at the edges or along the sidewall of the residual hard mask layer as claimed.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Shamim Ahmed whose telephone number is (571) 272-1457. The examiner can normally be reached on M-Thu (7:00-5:30) Every Friday Off.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine G. Norton can be reached on (571) 272-1465. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Shamim Ahmed Primary Examiner Art Unit 1765

SA May 15, 2006